

REMARKS

At the outset, the Examiner is thanked for the thorough review and consideration of the subject application. The final Office Action of October 27, 2003 has been received and contents carefully reviewed.

By this Amendment, Applicant amends claims 1 and 11, and adds claim 23. Claims 21-22 have been withdrawn as the result of the Examiner's constructive election in the Office Action dated October 27, 2003. Accordingly, claims 1, 3-7, 9-11 and 13-23 are currently pending in the present application. Reexamination and reconsideration of the application are respectfully requested.

In the Office Action, the Examiner rejected claims 1, 3-7, 9-11 and 13-20 are rejected under 35 U.S.C. § 103(a) as being unpatentable over the related art described in the present application (hereinafter "Related Art") in view of Taniguchi et al. (JP 2-58030A). Applicant respectfully traverses this rejection.

Claim 1 is allowable over the cited references in that claim 1 recites a combination of elements including, for example, "...wherein an entire area of the "E"-shaped channel is formed over the gate electrode, and the gate electrode underlies a part of the data line, the source electrodes and a part of the drain electrode." None of the cited references, singly or in combination, teaches or suggests at least this feature of the claimed invention. Accordingly, Applicant respectfully submits that claim 1 and claims 3-7 and 9-10, which depend therefrom, are allowable over the cited references.

Claim 11 is allowable over the cited references in that claim 11 recites a combination of elements including, for example, "...wherein an entire area of the "E"-shaped channel is formed over the gate electrode, and the gate electrode underlies a part of the data line, the source electrodes and a part of the drain electrode." None of the cited references, singly or in combination, teaches or suggests at least this feature of the claimed invention. Accordingly, Applicant respectfully submits that claim 11 and claims 13-20, which depend therefrom, are allowable over the cited references.

Claim 23 is allowable over the cited references in that claim 23 recites a combination of elements including, for example, "a source electrode and a drain electrode on the semiconductor

layer and adjacent the gate electrode, wherein the source electrode and the drain electrode oppose each other and each includes at least one protrusion that extends toward the opposing electrode... wherein the protrusions of the source and drain electrodes are formed within the area of the semiconductor layer." None of the cited references, singly or in combination, teaches or suggests at least this feature of the claimed invention. Accordingly, Applicant respectfully submits that claim 23 is allowable over the cited references.

Applicant believes the foregoing amendments place the application in condition for allowance and early, favorable action is respectfully solicited. If the Examiner deems that a telephone conference would further the prosecution of this application, the Examiner is invited to call the undersigned attorney at the telephone number (202) 496 - 7500. All correspondence should continue to be sent to the below-listed address.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911.

Dated: January 22, 2004

Respectfully submitted,

By 

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